

2nd National Conference on Recent Developments in Electronics (NCRDE 2017)

February 17-18, 2017

Jointly Organized by

IEEE EDS Delhi Chapter and Department of Electronic Science, University of Delhi South Campus

Sponsored by: Department of Science and Technology DST, Government of India &

Defense Research and Development Organisation DRDO

Venue: SP Jain Auditorium, University of Delhi South Campus, Benito Juarez Road, New Delhi-110021, India

One Day Short-Course

on

Design and RF Characterisation of GaN High Power Devices and amplifiers

Friday, February 17, 2017

Venue: S.P. Jain Centre Auditorium, University of Delhi South Campus, New Delhi

Technical Programme Schedule

09:30-10:00	Registration
10:00-10:15	Inauguration
10:15-11:00	Keynote Address : Dr. R. K. Sharma, Director, Solid State Physics Laboratory, Govt. of India
11:00-11:30	High Tea
11:30-12:15	Present status of GaN Technology Dr. Seema Vinayak, Scientist G, MMIC Division, Solid State Physics Laboratory, DRDO, Govt. of India
12:15-01:00	Design methodologies of power amplifiers Dr. Karun Rawat, Assistant Professor Department of Electronics and Communication, IIT-Roorkee
01:00-02:00	Lunch
02:00-02:45	RF Characterisation of GaN High power devices and circuits Dr. Sandeep Chaturvedi, GAETEC Hyderabad
02:45-03:30	Power Combining Techniques Mr. Umakan Goyal, Sc-E, MMIC Divison Solid State Physics Laboratory, DRDO, Govt. of India
03:30-03:45	Tea
03:45-04:15	Reliability issues in High power devices Dr. Meena Mishra, Scientist G, MMIC Division, Solid State Physics Laboratory, DRDO, Govt. of India
04:15-05:30	X parameters and Non-Linear Device Characterization Mr. Vishal Gupta, Segment and Team Lead, Sr. Applications Specialist (RF/MW) at Keysight Technologies